



Shantou Huashan Electronic Devices Co.,Ltd.

PNP SILICON TRANSISTOR

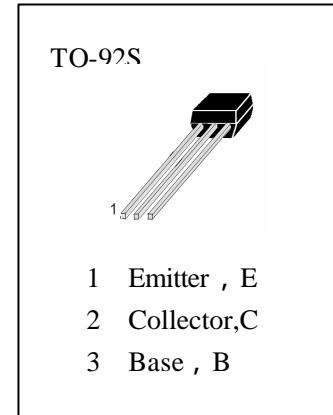
**HX1267**

## APPLICATIONS

Switching Applications .

## ABSOLUTE MAXIMUM RATINGS ( $T_a=25^\circ C$ )

$T_{stg}$	Storage Temperature.....	-55~150
$T_j$	Junction Temperature.....	150
$P_c$	Collector Dissipation.....	400mW
$V_{CBO}$	Collector-Base Voltage.....	-50V
$V_{CEO}$	Collector-Emitter Voltage.....	-50V
$V_{EBO}$	Emitter-Base Voltage.....	-5V
$I_c$	Collector Current.....	-150mA
$I_e$	Emitte Current.....	150mA



## ELECTRICAL CHARACTERISTICS ( $T_a=25^\circ C$ )

Symbol	Characteristics	Min	Typ	Max	Unit	Test Conditions
$I_{EBO}$	Emitter Cut-off Current			-0.1	$\mu A$	$V_{EB}=-5V, I_c=0$
$I_{CBO}$	Collector Cut-off Current			-0.1	$\mu A$	$V_{CB}=-50V, I_e=0$
$V_{CE(sat)}$	Collector- Emitter Saturation Voltage		-0.1	-0.3	V	$I_c=-100mA, I_b=-10mA$
$HFE$	DC Current Gain	70		400		$V_{CE}=-6V, I_c=-2mA$
$f_T$	Current Gain-Bandwidth Product	80			MHz	$V_{CE}=-10V, I_c=-1mA$
$C_{ob}$	Output Capacitance		4.0	7.0	pF	$V_{CB}=-10V, I_e=0, f=1MHz$
$NF$	Noise Figure		1.0	10	dB	$V_{CE}=-6V, I_c=-0.1mA$ $f=1KHz, R_g=10K$

## $h_{FE}$ Classification

O

Y

GR

70—140

120—240

200—400



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